

2SC3929, 2SC3929A

Silicon NPN epitaxial planer type

For low-frequency output amplification

Complementary to 2SA1531 and 2SA1531A

Features

- Low noise voltage NV.
- High forward current transfer ratio h_{FE} .
- S-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

Absolute Maximum Ratings (Ta=25°C)

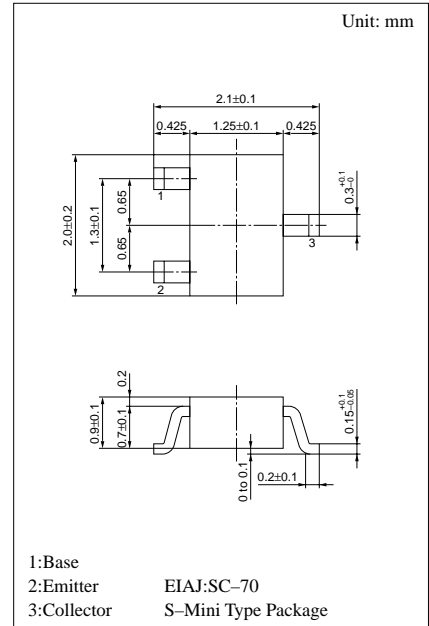
Parameter	Symbol	Ratings	Unit
Collector to base voltage	2SC3929	35	V
	2SC3929A	55	
Collector to emitter voltage	2SC3929	35	V
	2SC3929A	55	
Emitter to base voltage	V _{EBO}	5	V
Peak collector current	I _{CP}	100	mA
Collector current	I _C	50	mA
Collector power dissipation	P _C	150	mW
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55 ~ +150	°C

Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I _{CBO}	V _{CB} = 10V, I _E = 0			100	nA
	I _{CEO}	V _{CE} = 10V, I _B = 0			1	μA
Collector to base voltage	V _{CBO}	I _C = 10μA, I _E = 0	35			V
			55			
Collector to emitter voltage	V _{CEO}	I _C = 2mA, I _B = 0	35			V
			55			
Emitter to base voltage	V _{EBO}	I _E = 10μA, I _C = 0	5			V
Forward current transfer ratio	h _{FE} *	V _{CE} = 5V, I _C = 2mA	180		700	
Collector to emitter saturation voltage	V _{CE(sat)}	I _C = 100mA, I _B = 10mA			0.6	V
Base to emitter voltage	V _{BE}	V _{CE} = 1V, I _C = 100mA		0.7	1	V
Noise voltage	NV	V _{CE} = 10V, I _C = 1mA, G _v = 80dB R _g = 100kΩ, Function = FLAT			150	mV
Transition frequency	f _T	V _{CB} = 5V, I _E = -2mA, f = 200MHz		80		MHz

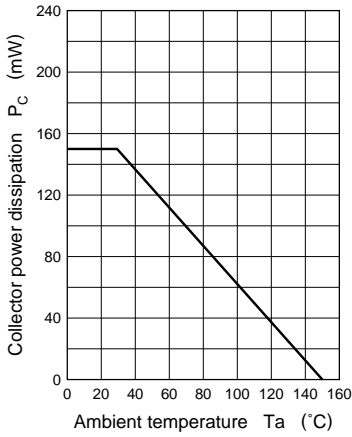
*¹h_{FE1} Rank classification

Rank	R	S	T
h _{FE}	180 ~ 360	260 ~ 520	360 ~ 700
Marking	2SC3929	SR	SS
Symbol	2SC3929A	TR	TS

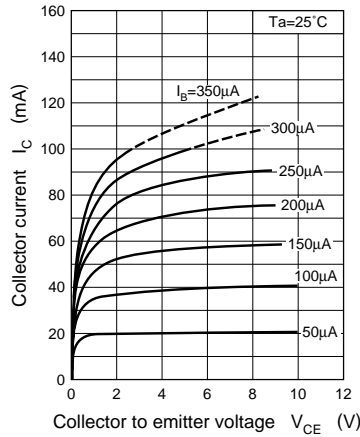


Marking symbol : S(2SC3929)
T(2SC3929A)

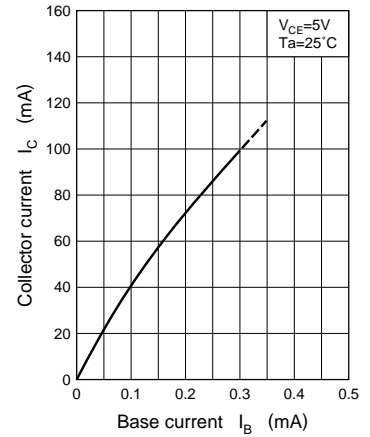
$P_C - T_a$



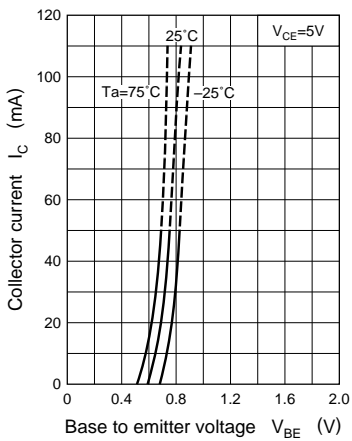
$I_C - V_{CE}$



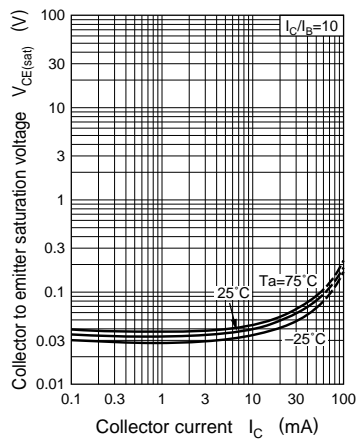
$I_C - I_B$



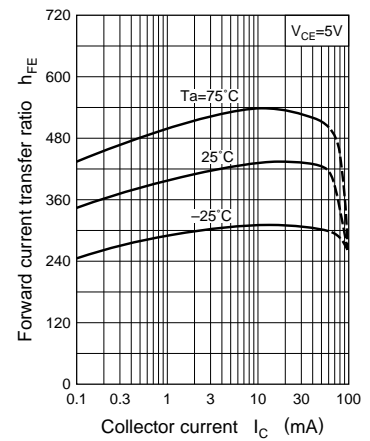
$I_C - V_{BE}$



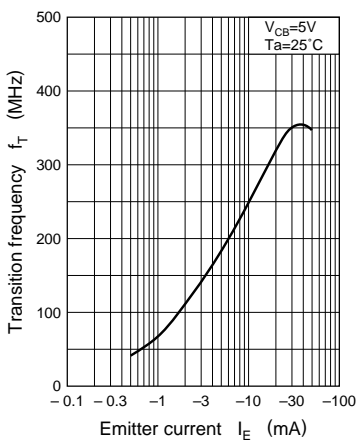
$V_{CE(sat)} - I_C$



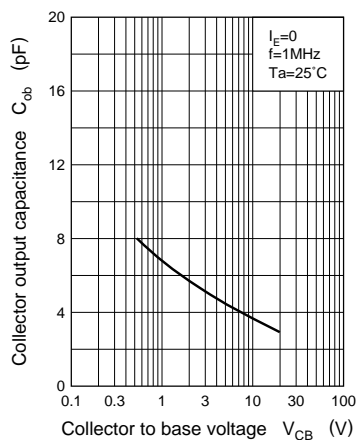
$h_{FE} - I_C$



$f_T - I_E$



$C_{ob} - V_{CB}$



$NV - V_{CE}$

